
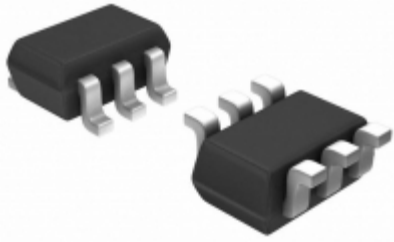



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|--|---|
|  | <h2 style="color: red;">SI1416EDH-T1-GE3</h2> |
|  <p>Image may be representation. See specs for product details.</p> | Hersteller-Teilenummer: SI1416EDH-T1-GE3 |
| | Hersteller / Marke: Vishay / Siliconix |
| | Teil der Beschreibung: MOSFET N-CH 30V 3.9A SOT-363 |
| | Datenblätter:  SI1416EDH-T1-GE3.pdf |
| | RoHs Status: Bleifrei / RoHS-konform |
| | Lagerzustand: New original, 81392 pcs Stock Available. |
| Liefern von: Hong Kong | |
| Versandweg: DHL/Fedex/TNT/UPS/EMS | |

Spezifikationen

| | |
|--|---|
| Teilenummer | SI1416EDH-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET N-CH 30V 3.9A SOT-363 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 81392 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | 6-TSSOP, SC-88, SOT-363 |
| Supplier Device-Gehäuse | SOT-363 |
| Verlustleistung (max) | 2.8W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 30V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 3.9A (Tc) |
| Rds On (Max) @ Id, Vgs | 58 mOhm @ 3.1A, 10V |
| VGS (th) (Max) @ Id | 1.4V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 12nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | - |
| Antriebsspannung (Max Rds On, Min Rds On) | 2.5V, 10V |
| Vgs (Max) | ±12V |
| Verpackung | Original-Reel® |

SI1416EDH-T1-GE3 ist neu im Original, Suche SI1416EDH-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1416EDH-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1416EDH-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|--|--|--|
|  <p>SI1413EDH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.3A SC-70-6</p> |  <p>SI1417DH-T1-E3 VISHAY SI1417DH-T1-E3 VISHAY</p> |  <p>SI1414DH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4A SOT-363</p> |  <p>SI1413EDH-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.3A SC70-6</p> |
|  <p>SI1414DH-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 4A SOT-363</p> |  <p>SI1416EDH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 3.9A SOT-363</p> |  <p>SI1417EDH-T1 VISHAY SI1417EDH-T1 VISHAY</p> |  <p>SI1417DH-T1-GE3 V SI1417DH-T1-GE3 V</p> |

heiße Teile

Mehr

| | | | | |
|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊗ SI1405DL-T1-E3 | ↔ SI1406DH | ⇒ SI1406DH-T1 | D SI1406DH-T1-E3 | ⇒ SI1406DH-T1-E3 |
| ⊣ SI1406DH-T1-GE3 | ⊗ SI1406DH-T1-GE3 | D SI1407DL | ⇒ SI1407DL-T1 | ⇒ SI1407DL-T1-E3 |
| ⊗ SI1407DL-T1-GE3 | ⊣ SI1410EDH | ⊗ SI1410EDH-T1 | ↔ SI1410EDH-T1-E3 | ⇒ SI1410EDH-T1-E3 |
| D SI1410EDH-T1-GE3 | ⊗ SI1413DH-T1 | ⊣ SI1413EDH | ⊗ SI1413EDH-T1 | ⇒ SI1413EDH-T1-E3 |
| ⇒ SI1413EDH-T1-E3 | ↔ SI1413EDH-T1-GE3 | ⊗ SI1413EDH-T1-GE3 | ⊣ SI1414DH-T1-GE3 | ⇒ SI1414DH-T1-GE3 |
| ↔ SI1416EDH-T1-GE3 | ⇒ SI1417DH-T1-E3 | D SI1417DH-T1-GE3 | ⊗ SI1417EDH-T1 | ⊣ SI1417EDH-T1-E3 |
| ⊗ SI1417EDH-T1-E3 | D SI1417EDH-T1-GE3 | ⇒ SI1417EDH-T1-GE3 | ↔ SI1422DH-T1-GE3 | ⇒ SI1422DH-T1-GE3 |
| ⊣ SI1424EDH-T1-GE3 | ⊗ SI1424EDH-T1-GE3 | ↔ SI1426DH-T1-E3 | ⇒ SI1426DH-T1-E3 | ⇒ SI1426DH-T1-GE3 |
| ⊗ SI1426DH-T1-GE3 | ⊣ SI1427EDH-T1-GE3 | ⊗ SI1427EDH-T1-GE3 | D SI1428EDH-T1-GE3 | ⇒ SI1428EDH-T1-GE3 |
| ↔ SI1433DH-T1 | ⊗ SI1433DH-T1-E3 | ⊣ SI1433DH-T1-E3 | ⊗ SI1433DH-T1-GE3 | ⇒ SI1433DH-T1-GE3 |

Contact us: Info@Y-IC.com

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